Independent Parallel Lithography

- Total Lithographed Area = 20,000 µm²
- Left Tip Patterned “N A” over “I”
- Right Tip Patterned “N O” over “V”
AFM Lithography: Defining a nMOSFET Gate

- Patterned Gate Length = 0.2 µm
- Effective Gate Length = 0.1 µm
- Transconductance = 279 mS/mm
- Threshold Voltage = 0.55 V